

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Withdrawn) A liquid crystal display device comprising:  
a thin film transistor formed over a substrate, the thin film transistor comprising:  
a gate electrode formed over the substrate;  
a gate insulating film formed over the gate electrode;  
a substantially intrinsic semiconductor layer formed over the gate insulating film;  
an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;  
at least one of a source and a drain electrodes formed over the n-type semiconductor layer;  
an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and  
a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

2. (Withdrawn) A liquid crystal display device comprising:  
a thin film transistor formed over a substrate, the thin film transistor comprising:  
a gate electrode formed over the substrate;  
a gate insulating film formed over the gate electrode;  
a substantially intrinsic semiconductor layer formed over the gate insulating film;  
an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

3. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

4. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

5. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

6. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer;

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes;

a first orientation film formed on the insulating film and on the pixel electrode;

a counter substrate opposing the substrate;

a counter electrode formed over the counter substrate;

a second orientation film formed over the counter electrode; and

a liquid crystal interposed between the substrate and the counter substrate.

7. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

8. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

9. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

10. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes;

a first orientation film formed on the insulating film and on the pixel electrode;

a counter substrate opposing the substrate;

a counter electrode formed over the second substrate;

a second orientation film formed over the counter electrode; and

a liquid crystal interposed between the substrate and the counter substrate.

11. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

12. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

13. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer;

a first orientation film formed on the insulating film and on the pixel electrode;

a counter substrate opposing the substrate;

a counter electrode formed over the counter substrate;

a second orientation film formed over the counter electrode; and

a liquid crystal interposed between the substrate and the counter substrate.

14. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic

semiconductor layer, wherein the insulating film is in contact with an edge of the n-type semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

15. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes;

a first orientation film formed on the insulating film and on the pixel electrode;

a counter substrate opposing the substrate;

a counter electrode formed over the counter substrate;

a second orientation film formed over the counter electrode; and

a liquid crystal interposed between the substrate and the counter substrate.

16. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:  
a gate electrode formed over the substrate;  
a gate insulating film formed over the gate electrode;  
a substantially intrinsic semiconductor layer formed over the gate insulating film;  
an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film;

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes;

a first orientation film formed on the insulating film and on the pixel electrode;

a counter substrate opposing the substrate;

a counter electrode formed over the counter substrate;

a second orientation film formed over the counter electrode; and

a liquid crystal interposed between the substrate and the counter substrate.

17. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

18. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a

contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

19. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer;

a first orientation film formed on the insulating film and on the pixel electrode;

a counter substrate opposing the substrate;

a counter electrode formed over the counter substrate;

a second orientation film formed over the counter electrode; and

a liquid crystal interposed between the substrate and the counter substrate.

20. (Withdrawn) A liquid crystal display device comprising:

a thin film transistor formed over a substrate, the thin film transistor comprising:

- a gate electrode formed over the substrate;
- a gate insulating film formed over the gate electrode;
- a substantially intrinsic semiconductor layer formed over the gate insulating film;
- an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

- at least one of a source and a drain electrodes formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

- an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, wherein the insulating film is in contact with an edge of the n-type semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

- a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer;

- a first orientation film formed on the insulating film and on the pixel electrode;

- a counter substrate opposing the substrate;

- a counter electrode formed over the counter substrate;

- a second orientation film formed over the counter electrode; and

- a liquid crystal interposed between the substrate and the counter substrate.

21. (Withdrawn) A liquid crystal display device according to any one of claims 1-20, wherein the substrate comprises one selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite, and polyimide.

22. (Withdrawn) A liquid crystal display device according to any one of claims 1-20, wherein the gate insulating film comprises silicon oxide or silicon nitride.

23. (Withdrawn) A liquid crystal display device according to any one of claims 1-20, wherein the substantially intrinsic semiconductor layer comprises amorphous silicon or microcrystalline silicon.

24. (Withdrawn) A liquid crystal display device according to any one of claims 1-20, wherein the at least one of the source and the drain electrodes comprises aluminum.

25. (Withdrawn) A liquid crystal display device according to any one of claims 1-20, wherein the insulating film comprising the resinous material comprises polyimide.

26. (Withdrawn) A liquid crystal display device according to any one of claims 1-20, wherein the pixel electrode comprises ITO.

27. (Withdrawn) A semiconductor device comprising:  
a filmy substrate;  
a thin film transistor formed over the filmy substrate, the thin film transistor having a channel forming region comprising silicon; and  
a layer comprising resin covering the thin film transistor.

28. (Currently Amended) A semiconductor device comprising:  
a flexible substrate;  
a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising silicon; and  
a layer comprising resin covering the thin film transistor.

wherein the semiconductor device is flexible.

29. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

30. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

31. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor.

32. (Currently Amended) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor,  
wherein the semiconductor device is flexible.

33. (Previously Presented) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

34. (Previously Presented) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

35. (Previously Presented) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors.

36. (Currently Amended) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors,

wherein the semiconductor device is flexible.

37. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid.

38. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid.

39. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

40. (Currently Amended) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation,

wherein the semiconductor device is flexible.

41. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

42. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

43. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor.

44. (Currently Amended) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor,

wherein the semiconductor device is flexible.

45. (Previously Presented) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

46. (Previously Presented) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

47. (Previously Presented) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor.

48. (Currently Amended) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor,

wherein the semiconductor device is flexible.

49. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

50. (Withdrawn) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

51. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a layer comprising resin covering the thin film transistor.

52. (Currently Amended) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a layer comprising resin covering the thin film transistor,

wherein the semiconductor device is flexible.

53. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

54. (Withdrawn) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

55. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween; and

a layer comprising resin covering the thin film transistor,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

56. (Currently Amended) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;  
a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween; and  
a layer comprising resin covering the thin film transistor,  
wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and  
wherein the crystalline silicon is formed by laser irradiation,  
wherein the semiconductor device is flexible.

57. (Withdrawn) A semiconductor device comprising:  
a pair of filmy substrates opposing to each other;  
a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween; and  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid,  
wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and  
wherein the crystalline silicon is formed by laser irradiation.

58. (Withdrawn) A semiconductor device comprising:  
a pair of flexible substrates opposing to each other;  
a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween; and  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid,  
wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and  
wherein the crystalline silicon is formed by laser irradiation.

59. (Withdrawn) A semiconductor device according to claims 27-34, wherein the silicon is amorphous silicon.

60. (Withdrawn) A semiconductor device according to claims 27-34, wherein the silicon is microcrystalline silicon.

61. (Currently Amended) A semiconductor device according to any one of claims 43-50, wherein the silicon is amorphous silicon.

62. (Currently Amended) A semiconductor device according to any one of claims 43-50, wherein the silicon is microcrystalline silicon.

63. (Previously Presented) A semiconductor device according to any one of claims 39-42 and 55-58, wherein the laser light comprises at least one selected from the group consisting of KrF excimer laser light and XeCl laser light.

64. (Withdrawn) A semiconductor device according to any one of claims 27, 29, 31, 33, 35, 37, 39, 41, 43, 45, 47, 49, 51, 53, 55 and 57, wherein the filmy substrate comprises a plastic substrate.

65. (Withdrawn) A semiconductor device according to any one of claims 27, 29, 31, 33, 35, 37, 39, 41, 43, 45, 47, 49, 51, 53, 55 and 57, wherein the filmy substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

66. (Previously Presented) A semiconductor device according to any one of claims 28, 30, 32, 34, 36, 38, 40, 42, 44, 46, 48, 50, 52, 54, 56 and 58, wherein the flexible substrate comprises a plastic substrate.

67. (Previously Presented) A semiconductor device according to any one of claims 28, 30, 32, 34, 36, 38, 40, 42, 44, 46, 48, 50, 52, 54, 56 and 58, wherein the flexible substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

68. (Previously Presented) A semiconductor device according to any one of claims 31-58, wherein the resinous layer comprises an acrylic resin.

69. (Previously Presented) A semiconductor device according to any one of claims 31-58, wherein the resinous layer comprises at least one selected from the group consisting of methyl esters of acrylic acid, ethyl esters of acrylic acid, butyl esters of acrylic acid, and 2-ethylhexyl esters of acrylic acid.

70. (Previously Presented) A semiconductor device according to any one of claims 27-58, wherein the thin film transistor comprises an inverted-staggered thin-film transistor.

71. (Previously Presented) A semiconductor device according to any one of claims 27-58, wherein the thin film transistor comprises a coplanar thin-film transistor.

72. (Currently Amended) A semiconductor device comprising:  
a flexible substrate processed with a heat treatment;

a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising silicon; and  
a layer comprising resin covering the thin film transistor,  
wherein the semiconductor device is flexible.

73. (Withdrawn) A semiconductor device comprising:  
a flexible substrate processed with a heat treatment;  
a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising silicon; and  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

74. (Currently Amended) A semiconductor device comprising:  
a flexible substrate;  
a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising crystalline silicon formed by a laser irradiation to amorphous silicon or microcrystalline silicon; and  
a layer comprising resin covering the thin film transistor,  
wherein the semiconductor device is flexible.

75. (Withdrawn) A semiconductor device comprising:  
a flexible substrate;  
a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising crystalline silicon formed by a laser irradiation to amorphous silicon or microcrystalline silicon; and  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

76. (Currently Amended) A semiconductor device comprising:  
a flexible substrate processed with a degas treatment;  
a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising silicon; and  
a layer comprising resin covering the thin film transistor,  
wherein the semiconductor device is flexible.

77. (Withdrawn) A semiconductor device comprising:  
a flexible substrate processed with a degas treatment;  
a thin film transistor formed over the flexible substrate, the thin film transistor having a channel forming region comprising silicon; and  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

78. (Currently Amended) A semiconductor device comprising:  
a flexible substrate;  
an inorganic insulating film formed over the flexible substrate;  
a semiconductor layer in contact with the inorganic insulating film; and  
a layer comprising resin covering the semiconductor layer and the inorganic insulating film,  
wherein the semiconductor device is flexible.

79. (Withdrawn) A semiconductor device comprising:  
a flexible substrate;  
an inorganic insulating film formed over the flexible substrate;  
a semiconductor layer in contact with the inorganic insulating film; and  
a silicon oxide film covering semiconductor layer and the inorganic insulating film,  
wherein the silicon oxide film is formed by applying a liquid.

80. (Previously Presented) A semiconductor device according to any one of claims 72-79, wherein the flexible substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

81. (Previously Presented) A semiconductor device according to claim 72 or 73, the heat treatment is performed above 200 °C.

82. (Previously Presented) A semiconductor device according to claim 74 or 75, wherein the laser light comprises KrF excimer laser light or XeCl laser light.

83. (Previously Presented) A semiconductor device according to claim 78 or 79, wherein the inorganic insulating film comprises a gate insulating film.

84. (Previously Presented) A semiconductor device according to claim 78 or 79, wherein the inorganic insulating film comprises a silicon oxide film or a silicon nitride film.